BGA2867

MMIC wideband amplifier

Rev. 5 — 3 October 2016

Product data sheet

1. Product profile

1.1 General description

Silicon Monolithic Microwave Integrated Circuit (MMIC) wideband amplifier with internal matching circuit in a 6-pin SOT363 plastic SMD package.

1.2 Features and benefits

- Internally matched to 50 Ω
- A gain of 26.4 dB at 2150 MHz
- Output power at 1 dB gain compression = 8 dBm
- Supply current = 21.7 mA at a supply voltage of 5.0 V
- Reverse isolation > 37 dB up to 2150 MHz
- Good linearity with low second order and third order products
- Noise figure = 3.6 dB at 950 MHz
- Unconditionally stable (K > 1)
- No output inductor required

1.3 Applications

- LNB IF amplifiers
- General purpose low noise wideband amplifier for frequencies between DC and 2.2 GHz

2. Pinning information

Table 1. Pinning

| Pin | Description | Simplified outline | Graphic symbol |
|------|-----------------|--------------------|------------------------------|
| 1 | V _{CC} | | |
| 2, 5 | GND2 | | |
| 3 | RF_OUT | | 6- |
| 4 | GND1 | 0 | 4 2,5 |
| 6 | RF_IN | □1 □2 □3 | 4 2,5 /// /// sym052 |
| | | | 3/11002 |



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3. Ordering information

Table 2. Ordering information

| Type number | Package | Package | | | | | | |
|-------------|---------|------------------------------------------|---------|--|--|--|--|--|
| | Name | Description | Version | | | | | |
| BGA2867 | - | plastic surface-mounted package; 6 leads | SOT363 | | | | | |

4. Marking

Table 3. Marking

| Type number | Marking code | Description |
|-------------|--------------|---------------------------|
| BGA2867 | LP* | * = - : made in Hong Kong |
| | | * = p : made in Hong Kong |
| | | * = W : made in China |
| | | * = t : made in Malaysia |

5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------------|-------------------------|-------------------------|------|------|------|
| V _{CC} | supply voltage | RF input AC coupled | -0.5 | +7.0 | V |
| I _{CC} | supply current | | - | 36 | mA |
| P _{tot} | total power dissipation | T _{sp} = 90 °C | - | 200 | mW |
| T _{stg} | storage temperature | | -40 | +125 | °C |
| Tj | junction temperature | | - | 125 | °C |
| P _{drive} | drive power | | - | +10 | dBm |

6. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Тур | Unit |
|-----------------------|--------------------------------------------------|----------------------------------------------------------|-----|------|
| R _{th(j-sp)} | thermal resistance from junction to solder point | $P_{tot} = 200 \text{ mW}; T_{sp} = 90 ^{\circ}\text{C}$ | 300 | K/W |

7. Characteristics

Table 6. Characteristics

 $V_{CC} = 5 \text{ V; } Z_S = Z_L = 50 \Omega; P_i = -34 \text{ dBm; } T_{amb} = 25 \text{ °C; measured on demo board; unless otherwise specified.}$

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|----------------|------------|------|------|------|------|
| V_{CC} | supply voltage | | 4.5 | 5.0 | 5.5 | V |
| I _{CC} | supply current | | 20.1 | 21.7 | 23.2 | mΑ |

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 Table 6.
 Characteristics ...continued

 $V_{CC} = 5 \text{ V; } Z_{S} = Z_{L} = 50 \text{ } \Omega; P_{i} = -34 \text{ dBm; } T_{amb} = 25 \text{ } ^{\circ}\text{C; } measured on demo board; unless otherwise specified.}$

| $\begin{array}{c} G_p & \text{power gain} & \begin{array}{c} f = 250 \text{ MHz} \\ \hline f = 950 \text{ MHz} \\ \hline f = 2150 \text{ MHz} \\ \end{array} \\ RL_{in} & \text{input return loss} & \begin{array}{c} f = 250 \text{ MHz} \\ \hline f = 250 \text{ MHz} \\ \hline f = 250 \text{ MHz} \\ \hline f = 2150 \text{ MHz} \\ \end{array} \\ RL_{out} & \text{output return loss} & \begin{array}{c} f = 250 \text{ MHz} \\ \hline f = 250 \text{ MHz} \\ \hline \end{array}$ | 25.8 26.4 24.9 19 18 19 13 17 | 26.3 27.1 26.4 21 20 25 17 | 26.9 27.8 27.9 23 22 31 | dB dB dB dB dB |
|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------------------------------------|----------------------------------------------|----------------------------------------|----------------------------|
| | 24.9 19 18 19 13 | 26.4 21 20 25 | 27.9 23 22 | dB dB dB |
| $ \begin{array}{c} {\sf RL_{in}} \\ {\sf Input \ return \ loss} \\ \\ \\ {\sf Input \ return \ loss} \\ \\ \\ {\sf Input \ return \ loss} \\ \\ \\ {\sf Input \ return \ loss} \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ $ | 19 18 19 13 17 | 21 20 25 | 23 22 | dB dB |
| f = 950 MHz f = 2150 MHz | 18 19 13 17 | 20 25 | 22 | dB |
| f = 2150 MHz | 19 13 17 | 25 | | |
| | 13 17 | | 31 | dB |
| RL out output return loss f = 250 MHz | 17 | 17 | | ab |
| | | | 21 | dB |
| f = 950 MHz | 12 | 18 | 19 | dB |
| f = 2150 MHz | 12 | 14 | 17 | dB |
| ISL isolation f = 250 MHz | 44 | 64 | 84 | dB |
| f = 950 MHz | 44 | 46 | 48 | dB |
| f = 2150 MHz | 34 | 37 | 39 | dB |
| NF noise figure f = 250 MHz | 3.2 | 3.7 | 4.2 | dB |
| f = 950 MHz | 3.2 | 3.6 | 4.1 | dB |
| f = 2150 MHz | 3.3 | 3.8 | 4.2 | dB |
| B _{-3dB} -3 dB bandwidth 3 dB below gain at 1 GHz | 2.8 | 3 | 3.2 | GHz |
| K Rollett stability factor f = 250 MHz | 29 | 36 | 38 | |
| f = 950 MHz | 3.5 | 4.5 | 4.5 | |
| f = 2150 MHz | 1 | 1.8 | 2.8 | |
| P _{L(sat)} saturated output power f = 250 MHz | 8 | 9 | 9 | dBm |
| f = 950 MHz | 7 | 8 | 10 | dBm |
| f = 2150 MHz | 5 | 6 | 7 | dBm |
| P _{L(1dB)} output power at 1 dB gain compression f = 250 MHz | 6 | 7 | 8 | dBm |
| f = 950 MHz | 5 | 7 | 8 | dBm |
| f = 2150 MHz | 4 | 5 | 6 | dBm |
| $IP3_I$ input third-order intercept point $P_{drive} = -40 \text{ dBm (for each tone)}$ | | | | |
| $f_1 = 250 \text{ MHz}; f_2 = 251 \text{ MHz}$ | -7 | - 5 | -3 | dBm |
| $f_1 = 950 \text{ MHz}; f_2 = 951 \text{ MHz}$ | -11 | -8 | -6 | dBm |
| $f_1 = 2150 \text{ MHz}; f_2 = 2151 \text{ MHz}$ | -16 | -13 | -10 | dBm |
| IP3 _O output third-order intercept point $P_{drive} = -40 \text{ dBm (for each tone)}$ | | | | |
| $f_1 = 250 \text{ MHz}; f_2 = 251 \text{ MHz}$ | 19 | 21 | 23 | dBm |
| $f_1 = 950 \text{ MHz}; f_2 = 951 \text{ MHz}$ | 17.5 | 19.5 | 21.5 | dBm |
| $f_1 = 2150 \text{ MHz}$; $f_2 = 2151 \text{ MHz}$ | 11 | 14 | 17 | dBm |
| $P_{L(2H)}$ second harmonic output power $P_{drive} = -37 \text{ dBm}$ | | | | |
| $f_{1H} = 250 \text{ MHz}; f_{2H} = 500 \text{ MHz}$ | -63 | -61 | -59 | dBm |
| $f_{1H} = 950 \text{ MHz}; f_{2H} = 1900 \text{ MHz}$ | - | -50 | - | dBm |
| $\Delta IM2$ second-order intermodulation distance $P_{drive} = -40 \text{ dBm (for each tone)}$ | | | | |
| $f_1 = 250 \text{ MHz}; f_2 = 251 \text{ MHz}$ | 49 | 51 | 53 | dBc |
| $f_1 = 950 \text{ MHz}; f_2 = 951 \text{ MHz}$ | - | 51 | - | dBc |

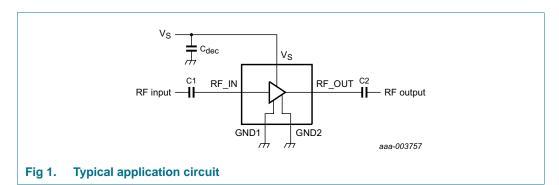
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8. Application information

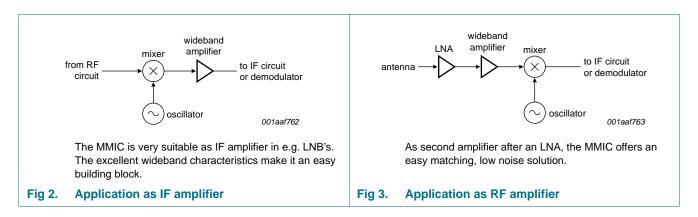
<u>Figure 1</u> shows a typical application circuit for the BGA2867 MMIC. The device is internally matched to $50~\Omega$, and therefore does not need any external matching. The value of the input and output DC blocking capacitors C2 and C3 should not be more than 100 pF for applications above 100 MHz. However, when the device is operated below 100 MHz, the capacitor value should be increased.

The location of the 470 pF supply decoupling capacitor (C_{dec}) can be precisely chosen for optimum performance.

The PCB top ground plane, connected to pins 2, 4 and 5 must be as close as possible to the MMIC, preferably also below the MMIC. When using via holes, use multiple via holes as close as possible to the MMIC.



8.1 Application examples



8.2 Tables

Table 7. Supply current over temperature and supply voltages *Typical values.*

| Symbol | Parameter | Conditions | T _{amb} (°C) | | | Unit | |
|-----------------|----------------|-------------------------|-----------------------|-------|-------|------|--|
| | | | -40 | +25 | +85 | | |
| I _{CC} | supply current | V _{CC} = 4.5 V | 21.90 | 20.10 | 18.60 | mA | |
| | | V _{CC} = 5.0 V | 23.50 | 21.70 | 20.10 | mA | |
| | | V _{CC} = 5.5 V | 25.00 | 23.20 | 21.60 | mA | |

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Table 8. Second harmonic output power over temperature and supply voltages *Typical values*.

| Symbol | Parameter | Conditions | T _{amb} (°C) | | Unit | |
|--------------------|------------------------------|----------------------------------------------------|-----------------------|-----|------|-----|
| | | | -40 | +25 | +85 | |
| P _{L(2H)} | second harmonic output power | $f = 250 \text{ MHz}; P_{drive} = -37 \text{ dBm}$ | | | | |
| | | V _{CC} = 4.5 V | -75 | -67 | -62 | dBm |
| | | V _{CC} = 5.0 V | -63 | -61 | -58 | dBm |
| | | V _{CC} = 5.5 V | -59 | -58 | -56 | dBm |
| | | $f = 950 \text{ MHz}; P_{drive} = -37 \text{ dBm}$ | | | | |
| | | V _{CC} = 4.5 V | -51 | -51 | -50 | dBm |
| | | V _{CC} = 5.0 V | -50 | -50 | -49 | dBm |
| | | V _{CC} = 5.5 V | -49 | -49 | -48 | dBm |

Table 9. Input power at 1 dB gain compression over temperature and supply voltages *Typical values*.

| Symbol | arameter | Conditions | T _{amb} (°C) | | | Unit |
|---------------------|--------------------------------------|-------------------------|-----------------------|-----|-----|------|
| | | | -40 | +25 | +85 | |
| P _{i(1dB)} | input power at 1 dB gain compression | f = 250 MHz | | | | |
| | | V _{CC} = 4.5 V | -19 | -19 | -19 | dBm |
| | | V _{CC} = 5.0 V | -18 | -19 | -19 | dBm |
| | | V _{CC} = 5.5 V | -18 | -18 | -19 | dBm |
| | | f = 950 MHz | | | | |
| | | V _{CC} = 4.5 V | -20 | -20 | -20 | dBm |
| | | V _{CC} = 5.0 V | -19 | -20 | -20 | dBm |
| | | V _{CC} = 5.5 V | -19 | -19 | -20 | dBm |
| | | f = 2150 MHz | | | | |
| | | V _{CC} = 4.5 V | -21 | -22 | -23 | dBm |
| | | V _{CC} = 5.0 V | -21 | -22 | -23 | dBm |
| | | V _{CC} = 5.5 V | -21 | -22 | -23 | dBm |

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Table 10. Output power at 1 dB gain compression over temperature and supply voltages *Typical values*.

| Symbol | Parameter | Conditions | T _{amb} (°C) | | | Unit |
|---------------------|---------------------------------------|-------------------------|-----------------------|-----|-----|------|
| | | | -40 | +25 | +85 | |
| P _{L(1dB)} | output power at 1 dB gain compression | f = 250 MHz | | | | |
| | | V _{CC} = 4.5 V | 7 | 6 | 5 | dBm |
| | | V _{CC} = 5.0 V | 7 | 7 | 6 | dBm |
| | | V _{CC} = 5.5 V | 8 | 8 | 7 | dBm |
| | | f = 950 MHz | | | | |
| | | V _{CC} = 4.5 V | 6 | 6 | 5 | dBm |
| | | V _{CC} = 5.0 V | 7 | 7 | 6 | dBm |
| | | V _{CC} = 5.5 V | 8 | 7 | 6 | dBm |
| | | f = 2150 MHz | | | | |
| | | V _{CC} = 4.5 V | 5 | 4 | 2 | dBm |
| | | V _{CC} = 5.0 V | 6 | 5 | 3 | dBm |
| | | V _{CC} = 5.5 V | 7 | 5 | 3 | dBm |

Table 11. Saturated output power over temperature and supply voltages *Typical values*.

| Symbol | Parameter | Conditions | T _{amb} | (°C) | | Unit |
|---------------------|------------------------|-------------------------|------------------|------|-----|------|
| | | | -40 | +25 | +85 | |
| P _{L(sat)} | saturated output power | f = 250 MHz | | | | |
| | | V _{CC} = 4.5 V | 8 | 8 | 8 | dBm |
| | | V _{CC} = 5.0 V | 10 | 9 | 8 | dBm |
| | | V _{CC} = 5.5 V | 10 | 10 | 9 | dBm |
| | | f = 950 MHz | | | | |
| | | V _{CC} = 4.5 V | 8 | 8 | 7 | dBm |
| | | V _{CC} = 5.0 V | 9 | 8 | 8 | dBm |
| | | V _{CC} = 5.5 V | 10 | 9 | 8 | dBm |
| | | f = 2150 MHz | | | | |
| | | V _{CC} = 4.5 V | 6 | 5 | 4 | dBm |
| | | V _{CC} = 5.0 V | 7 | 6 | 4 | dBm |
| | | V _{CC} = 5.5 V | 8 | 6 | 5 | dBm |

Table 12. Second-order intermodulation distance over temperature and supply voltages *Typical values.*

| Symbol | Parameter | Conditions | T _{amb} | T _{amb} (°C) | | |
|--------|---------------------------------------|---------------------------------------------------------------------------------------|------------------|-----------------------|-----|-----|
| | | | -40 | +25 | +85 | |
| ΔΙΜ2 | second-order intermodulation distance | $f_1 = 250 \text{ MHz};$ $f_2 = 251 \text{ MHz};$ $P_{drive} = -40 \text{ dBm}$ | | | | |
| | | V _{CC} = 4.5 V | 43 | 46 | 51 | dBc |
| | | V _{CC} = 5.0 V | 48 | 51 | 58 | dBc |
| | | V _{CC} = 5.5 V | 52 | 56 | 69 | dBc |
| | | $f_1 = 950 \text{ MHz};$ $f_2 = 951 \text{ MHz};$ $P_{drive} = -40 \text{ dBm}$ | | | | |
| | | V _{CC} = 4.5 V | 40 | 45 | 55 | dBc |
| | | V _{CC} = 5.0 V | 45 | 51 | 63 | dBc |
| | | V _{CC} = 5.5 V | 50 | 60 | 52 | dBc |

Table 13. Output third-order intercept point over temperature and supply voltages *Typical values*.

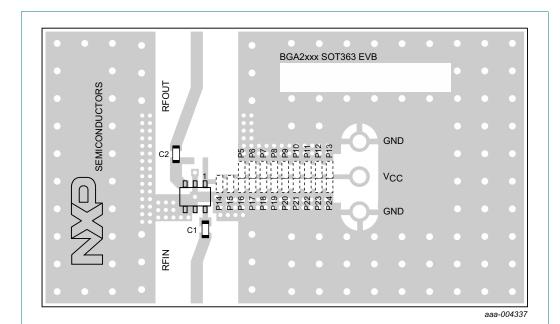
| Symbol IP3 _O | Parameter output third-order intercept point | Conditions | T _{amb} | T _{amb} (°C) | | |
|-------------------------|-----------------------------------------------|-----------------------------------------------------------------------------------------|------------------|-----------------------|------|-----|
| | | | -40 | +25 | +85 | |
| | | $f_1 = 250 \text{ MHz};$ $f_2 = 251 \text{ MHz};$ $P_{drive} = -40 \text{ dBm}$ | | | | |
| | | V _{CC} = 4.5 V | 21 | 19 | 18 | dBm |
| | | V _{CC} = 5.0 V | 23 | 21 | 20 | dBm |
| | | V _{CC} = 5.5 V | 24 | 23 | 21 | dBm |
| | | $f_1 = 950 \text{ MHz};$ $f_2 = 951 \text{ MHz};$ $P_{drive} = -40 \text{ dBm}$ | | | | |
| | | V _{CC} = 4.5 V | 18 | 17 | 16 | dBm |
| | | V _{CC} = 5.0 V | 20.5 | 19.5 | 18.5 | dBm |
| | | V _{CC} = 5.5 V | 21 | 20 | 18 | dBm |
| | | $f_1 = 2150 \text{ MHz};$ $f_2 = 2151 \text{ MHz};$ $P_{drive} = -40 \text{ dBm}$ | | | | |
| | | V _{CC} = 4.5 V | 14 | 13 | 11 | dBm |
| | | V _{CC} = 5.0 V | 16 | 14 | 12 | dBm |
| | | V _{CC} = 5.5 V | 17 | 15 | 12 | dBm |

Table 14. —3 dB bandwidth over temperature and supply voltages Typical values.

| Typical values. | | | | | | |
|-------------------|-----------------|--------------------------|-----------------------|------|------|-----|
| Symbol | Parameter | Conditions | T _{amb} (°C) | | Unit | |
| | | | -40 | +25 | +85 | |
| B _{-3dB} | -3 dB bandwidth | V _{CC} = 4.5 V | 3.09 | 2.98 | 2.84 | GHz |
| | | $V_{CC} = 5.0 \text{ V}$ | 3.11 | 3.00 | 2.91 | GHz |
| | | $V_{CC} = 5.5 \text{ V}$ | 3.13 | 3.01 | 2.93 | GHz |

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9. Test information



For decoupling a decoupling capacitor (C_{dec}) is used on one of the positions of P5 to P24. The results mentioned in this data sheet have been obtained using the decoupling capacitor C_{dec} on position P22. The distance between the center of pin 1 and the center of position P22 is 7.43 mm.

Fig 4. PCB layout and demo board with components

Table 15. List of components used for the typical application

| Component | Description | Value | Dimensions | Remarks |
|---------------|-----------------------------------------------------------------|--------|------------|-----------------------------|
| C1, C2 | multilayer ceramic chip capacitor | 470 pF | 0603 | X7R RF coupling capacitor |
| P5 to P24 [1] | position for multilayer ceramic chip capacitor C _{dec} | 470 pF | 0603 | X7R RF decoupling capacitor |
| IC1 | BGA2867 MMIC | - | SOT363 | |

[1] For decoupling a decoupling capacitor (C_{dec}) is used on one of the positions of P5 to P24. The results mentioned in this data sheet have been obtained using the decoupling capacitor C_{dec} on position P22.

10. Package outline

Plastic surface-mounted package; 6 leads

SOT363

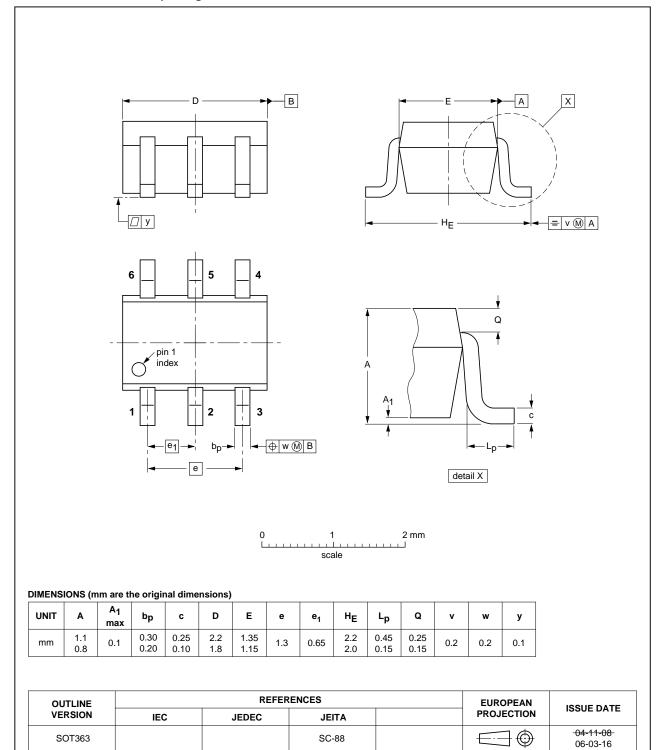


Fig 5. Package outline SOT363

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MMIC wideband amplifier

11. Abbreviations

Table 16. Abbreviations

| Acronym | Description |
|---------|---------------------------|
| IF | Intermediate Frequency |
| LNA | Low-Noise Amplifier |
| LNB | Low-Noise Block converter |
| PCB | Printed-Circuit Board |
| SMD | Surface Mounted Device |

12. Revision history

Table 17. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes | |
|----------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------------|---------------|-------------|--|
| BGA2867 v.5 | 20161003 | Product data sheet | - | BGA2867 v.4 | |
| Modifications: | Table 6 on page 2: the min/max value for P_{L(2H)} (f_{1H} = 950 MHz; f_{2H} = 1900 MHz) removed Table 6 on page 2: the min/max value for ΔIM2 (f₁ = 950 MHz; f₂ = 951 MHz) has been removed | | | | |
| BGA2867 v.4 | 20150713 | Product data sheet | - | BGA2867 v.3 | |
| Modifications: | The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. | | | | |
| BGA2867 v.3 | 20130827 | Product data sheet | - | BGA2867 v.2 | |
| BGA2867 v.2 | 20120925 | Product data sheet | - | BGA2867 v.1 | |
| BGA2867 v.1 | 20120312 | Product data sheet | - | - | |

MMIC wideband amplifier

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13.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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- [2] The term 'short data sheet' is explained in section "Definitions"
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BGA2867 NXP Semiconductors

MMIC wideband amplifier

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